

VDS	RDS(on)	ID@25°C
1200V	25mΩ	90A

#### Applications:

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- EV Charging
- Motor Drives

#### Features:

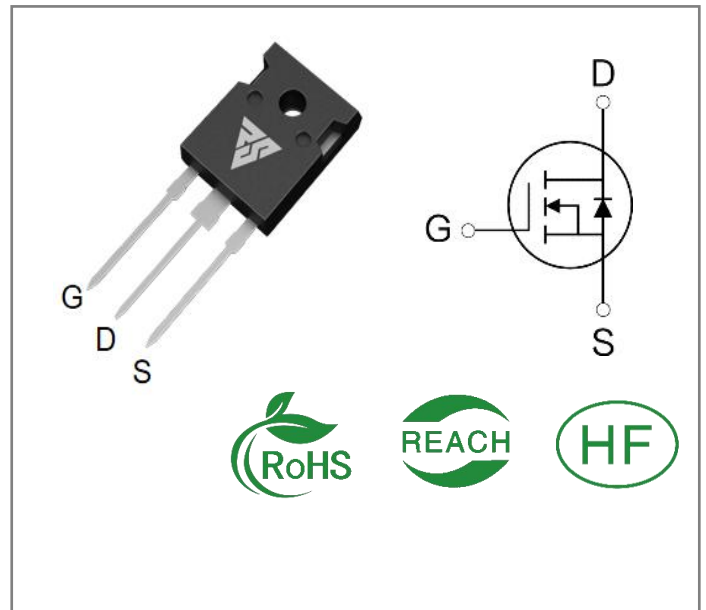
- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness

#### Benefits:

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

#### Ordering Information

Part Number	Package	Marking	Packing	Qty.
RSM120025W	TO-247-3	RSM120025W	Tube	30 PCS



#### Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VDSmax	Drain - Source Voltage	1200	V	VGS=0V, ID =100μA	
VGSmax	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
VGSop	Gate - Source Voltage	-5/+20	V	Recommended operational values	
ID	Continuous Drain Current	90 60	A	VGS=20V, TC =25°C VGS=20V, TC =100°C	
ID(pulse)	Pulsed Drain Current	200	A	Pulse width tp limited by TJmax	
PD	Power Dissipation	370	W	TC =25°C, TJ =150°C	
TL	Solder Temperature	260	°C		
TJ, Tstg	Operating Junction and Storage Temperature	-40 to +150	°C		

**Electrical Characteristics** (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V(BR) <sub>DS</sub>	Drain-Source Breakdown Voltage	1200			V	V <sub>GS</sub> =0V, I <sub>D</sub> =100μA	
V <sub>GS(th)</sub>	Gate Threshold Voltage	2.0	2.4	4.0	V	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>DS</sub> =15mA, TC =25°C	
			1.8		V	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>DS</sub> =15mA, TC =150°C	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current		1	100	μA	V <sub>DS</sub> = 1200V, V <sub>GS</sub> =0V	
I <sub>GSS</sub>	Gate-Source Leakage Current			250	nA	V <sub>GS</sub> =20V, V <sub>DS</sub> = 0V	
R <sub>DS(on)</sub>	Drain-Source on-state Resistance		25	34	mΩ	V <sub>GS</sub> =20V, I <sub>D</sub> =50A, TC =25°C	
			43			V <sub>GS</sub> =20V, I <sub>D</sub> =50A, TC =150°C	
C <sub>iss</sub>	Input Capacitance		3600		pF	V <sub>GS</sub> =0V, V <sub>DS</sub> =1000 V, f=1MHz, V <sub>AC</sub> =25 mV	
C <sub>oss</sub>	Output Capacitance		24				
C <sub>rss</sub>	Reverse Transfer Capacitance		16				
E <sub>ON</sub>	Turn-On Switching Energy		1800		μJ	V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/20V, I <sub>D</sub> = 30A, R <sub>G(ext)</sub> = 2.5Ω, L= 200μH	
E <sub>OFF</sub>	Turn-Off Energy		1500				
t <sub>d(on)</sub>	Turn-On Delay Time		16		ns	V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/20 V, I <sub>D</sub> = 30A, R <sub>G(ext)</sub> =2. 5 Ω , R <sub>L</sub> =2.5Ω	
t <sub>r</sub>	Rise Time		16.2				
t <sub>d(off)</sub>	Turn-Off Delay Time		33				
t <sub>f</sub>	Fall Time		7.8				
R <sub>G(int)</sub>	Internal Gate Resistance		2.0		Ω	f=1 MHz, V <sub>AC</sub> =25mV	
Q <sub>gs</sub>	Gate to Source Charge		54		nC	V <sub>DS</sub> =800V, V <sub>GS</sub> =-5/20V, I <sub>D</sub> =30A	
Q <sub>gd</sub>	Gate to Drain Charge		29		nC		
Q <sub>g</sub>	Total Gate Charge		195				

**Reverse Diode Characteristics** (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max	Unit	Test Conditions	Note
VSD	Diode Forward Voltage	3.6		V	VGS=-5V, ISD =25 A, TJ = 25°C	
		3.3		V	VGS=-5V, ISD=25 A, TJ= 150°C	
IS	Continuous Diode Forward Current		90	A	VGS=-5V, TC= 25°C	
trr	Reverse Recovery time	55		ns	ISD= 25A, VR = 800V	
Qrr	Reverse Recovery Charge	320		nC		
Irrm	Peak Reverse Recovery Current	10.7		A		

**Thermal Characteristics** (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
RθJC	Thermal Resistance from Junction to Case	0.25	°C/W		
RθJA	Thermal Resistance From Junction to Ambient	40			

Typical Feature Curve

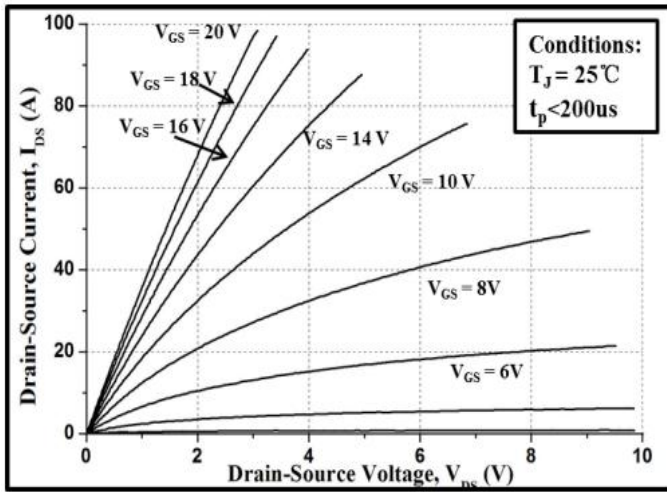


Figure 1. Typical Output Characteristics  $T_J=25^\circ\text{C}$

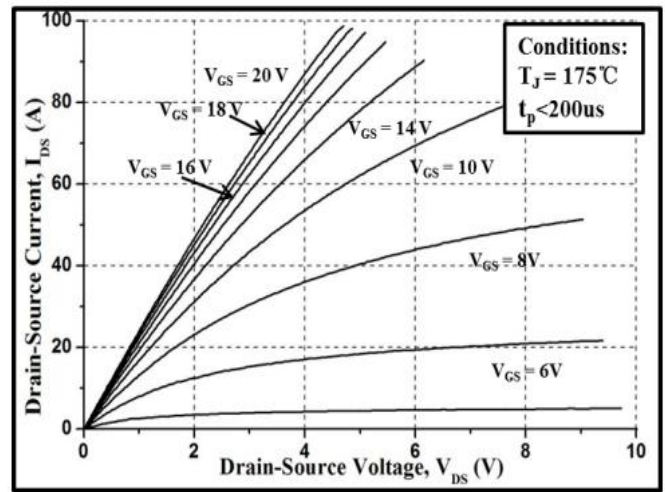


Figure 2. Typical Output Characteristics  $T_J=175^\circ\text{C}$

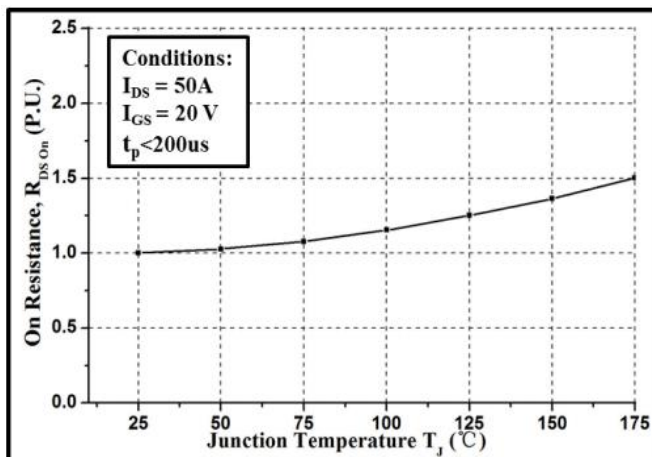


Figure 3. Normalized On-Resistance vs. Temperature

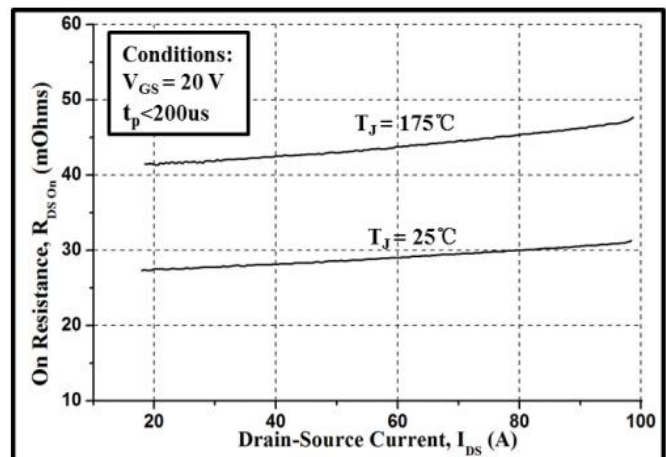


Figure 4. On-Resistance vs. Drain Current

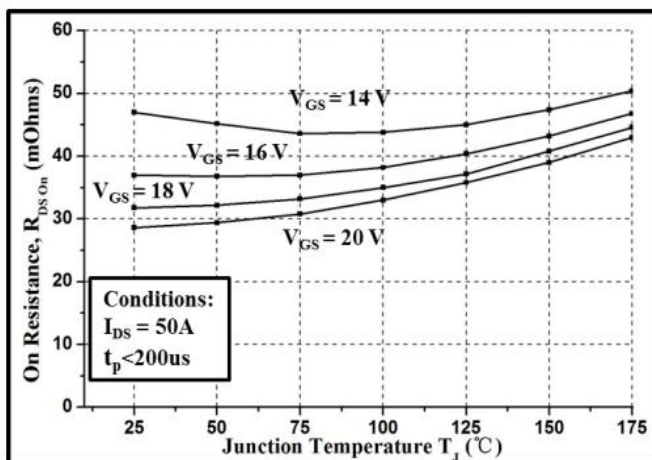


Figure 5. On-Resistance vs. Temperature

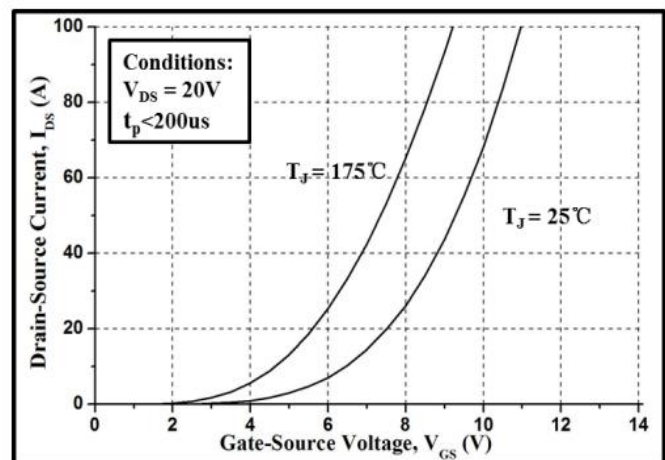


Figure 6. Typical Transfer Characteristics

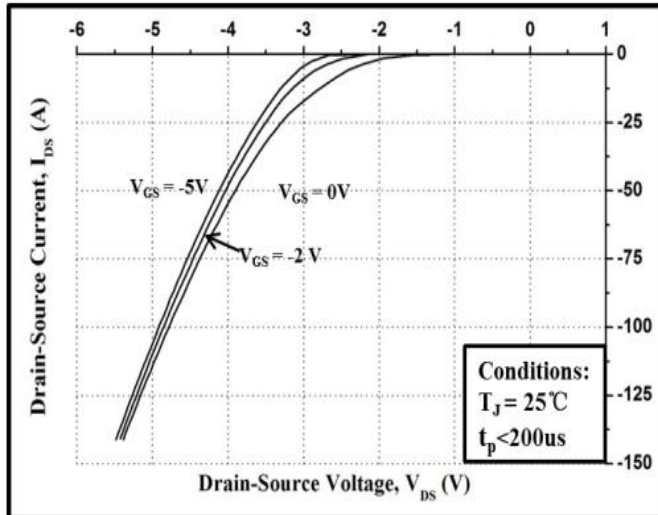


Figure 7. Body Diode Characteristics at 25°C

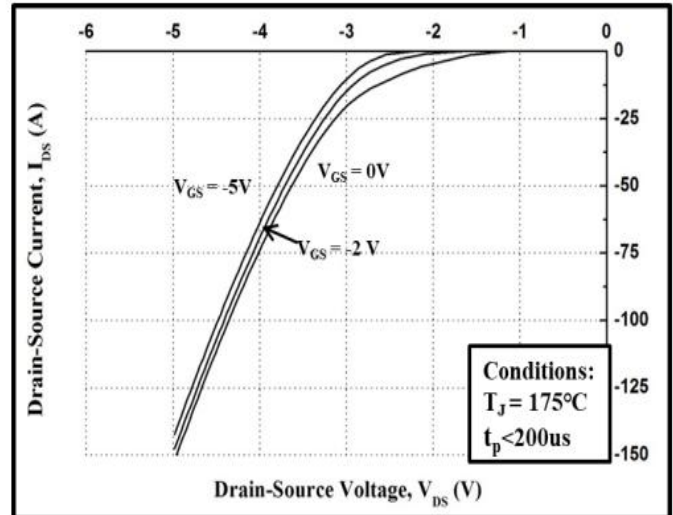


Figure 8. Body Diode Characteristics at 175°C

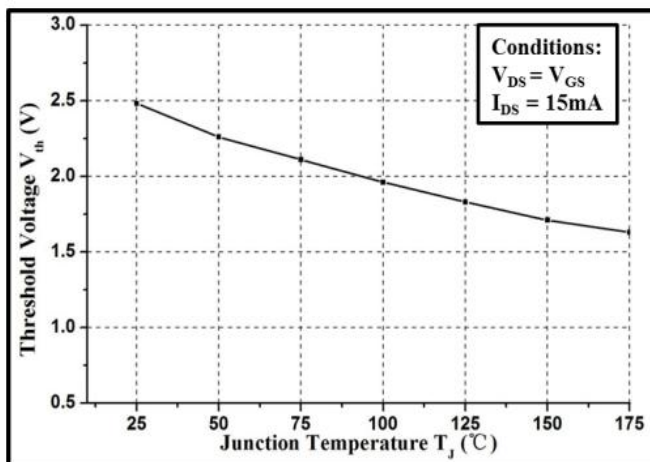


Figure 9. Gate Threshold Voltage vs. Temperature

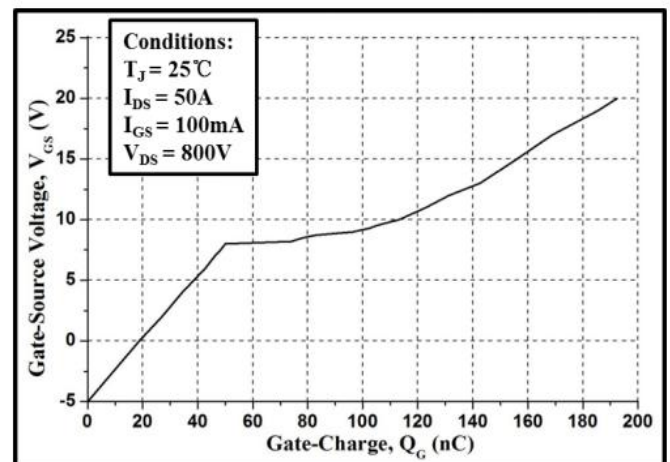


Figure 10. Gate Charge Characteristic

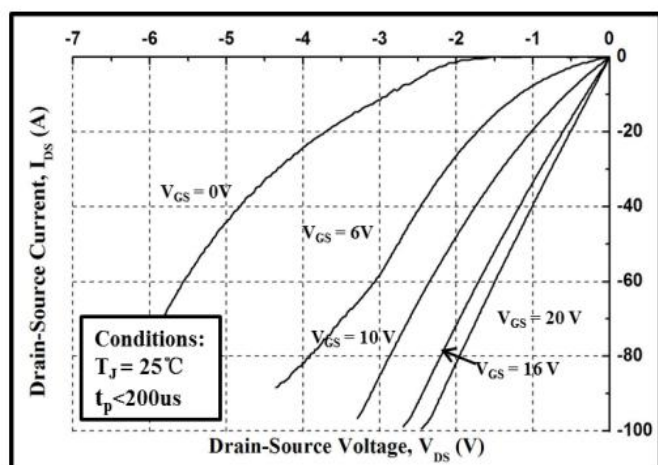


Figure 11. 3<sup>rd</sup> Quadrant Characteristics at 25° C

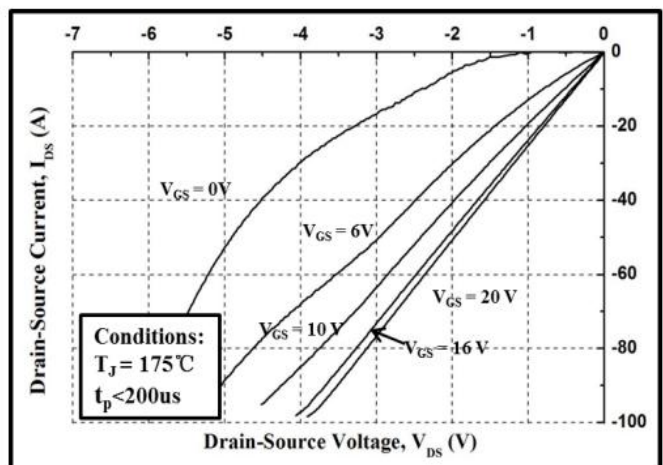


Figure 12. 3<sup>rd</sup> Quadrant Characteristics at 175° C



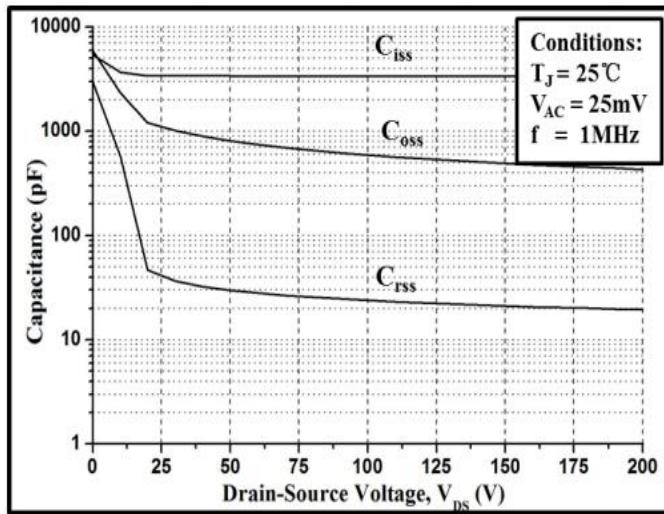


Figure 13. Capacitances vs. Drain-Source Voltage

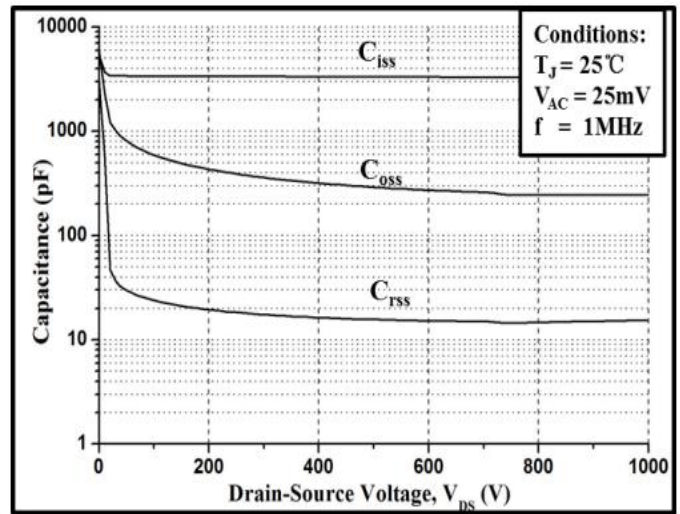
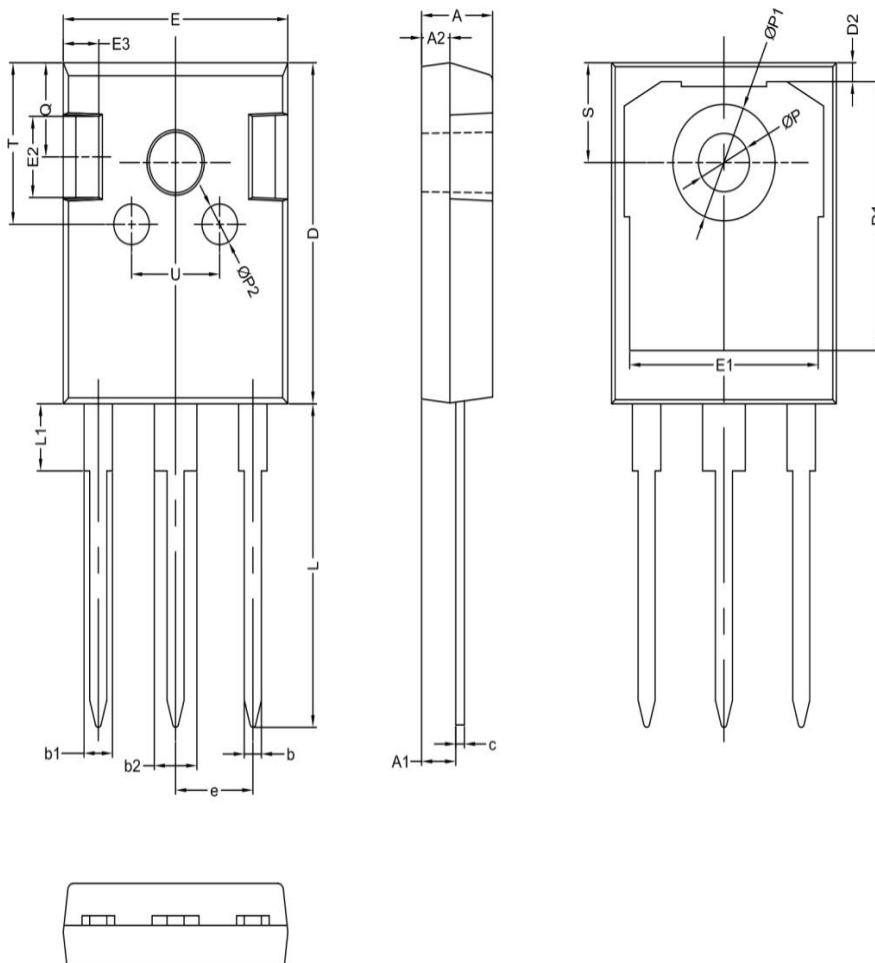


Figure 14. Capacitances vs. Drain-Source Voltage

**Package outline drawing(TO-247-3 Unit: mm )**



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
b2		3.00	
c	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.55	
D2		1.20	
E	15.60	15.80	16.0
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	-	-	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

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